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U.S. DEPARTMENT OF COMMERCE (REV. 05/03) PATENT AND TRADEMARK OFFICE				ATTY. DOCKET NO. BU-021AX	APPLICATION NO. 10/790,403	
O I P INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				APR 29 2004 U.S. PATENT AND TRADEMARK OFFICE JCT 108		
				APPLICANT: M. Selim Unlu et al.		
				FILING DATE March 1, 2004	TC ART UNIT	
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MW	US 5,770,511	06/23/1998	Matsumoto et al	438	406	
MW	US 5,376,215	12/27/1994	Ohta et al	156	345	
MW	US 4,670,765	06/02/1987	Nakamura et al	357	30	
MW	US 5,757,986	05/26/1998	Crampton et al	385	2	
MW	US 5,767,507	06/16/1998	Unlu et al	250	225	
MW	US 5,710,057	01/20/1998	Kenney	437	62	
MW	US 5,671,914	09/30/1997	Kalkhoran et al	257	77	
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MW	Ishikawa et al., "Epitaxy-ready Si/SiO <sub>2</sub> Bragg Reflectors by Multiple Separation-by-Implanted Oxygen", Appl. Phys. Letters, Vol 69, No. 25 16 December 1996.					
MW	Sinnis et al. "Silicon-based Resonant-cavity-enhanced Photodiode with a Buried SiO <sub>2</sub> Reflector", Appl. Phys. Letters, Vol 74, No. 9, 1 March 1999.					
MW	Schow et al., "Design and Implementation of High-speed Planar Si Photodiodes Fabricated on SOI Substrates", IEEE Journal of Quantum Electronics, Vol. 35, No. 10, October 1999.					
MW	Schaub et al., "Resonant-cavity-enhanced High-speed Si Photodiode Grown by Epitaxial Lateral Overgrowth", IEEE Photonics Technology Letters, Vol. 11, No. 12, 12 December 1999.					
MW	Jalali et al., "Advances in Silicon-on-Insulator Optoelectronics", IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No. 6, Nov/Dec 1998.					
MW	Fukatsu et al., "Spectral Modulation of Luminescence of Strained Si <sub>1-x</sub> Ge <sub>x</sub> /Si Quantum Wells in a Vertical Cavity with air/Si and Si/SiO <sub>2</sub> Interface Mirrors", Appl. Phys. Letters, Vol. 65, No. 24, 12 December 1994.					
EXAMINER	MW/czewski		DATE CONSIDERED		02/2006	
•EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						

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MW	US 5,498,863	03/12/1996	Miller	250	214.1	
MW	US 5,389,797	02/14/1995	Bryan et al	257	21	
MW	US 5,455,421	10/03/1995	Spears	250	338.4	
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MW	US 5,793,060	08/11/1998	Morikawa	257	85	

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MW	Yonehara et al., "Epitaxial Layer Transfer by Bond and Etch Back of Porous Si", Appl Phys. Letters, Vol. 64, No. 16, 18 April 1994.
MW	Tan et al., "Modeling and Performance of Wafer-Fused Resonant-Cavity Enhanced Photodetectors", IEEE Journal of Quantum Electronics, Vol. 31, No. 10, 10 October 1995.
MW	Bean et al., "High-Speed Polysilicon Resonant-Cavity Photodiode with SiO <sub>2</sub> -Si Bragg Reflectors", IEEE Photonics Technology Letters, Vol. 9, No. 6, June 1997.
MW	Diaz et al., "Si/SiO <sub>2</sub> Resonant Cavity Photodetector", Appl. Phys. Letters, Vol. 69, No. 19, 4 November 1996.
MW	Murtaza et al., "Short-Wavelength, High-Speed, Si-Based Resonant-Cavity Photodetector", IEEE Photonics Technology Letters, Vol. 8, No. 7, July 1996.
MW	Sato et al., "High-Quality Epitaxial Layer Transfer (ELTRAN) by Bond And Etch-Back of Porous Si", Proceedings of 1995 IEEE International SOI Conference, October 1995.

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MW	US 5,374,564	12/20/94	Bruel	437	24	
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MW	Wada et al., "A New Approach of Photonic Bandgap Formation-Wafer Bonding and Delamination Technique", Extended Abstracts of the 1998 International Conference on Solid State Devices and Materials, pp 382-383 1998.
MW	Unlu et al., "Resonant Cavity Enhanced Photonic Devices", Journal Appl. Phys. Vol. 78, No. 2, 15 July 1995.

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